

# SM5023 series Miniature-package Crystal Oscillator Module ICs

# **OVERVIEW**

The SM5023 series are 3rd overtone crystal oscillator module ICs. They feature built-in oscillator capacitors with excellent frequency response. As cutoff frequency can be configured by using an external feedback resistor  $R_{fo}$ , a favorable 3rd overtone oscillation can be realized with a few external components. The oscillator circuit characteristics are optimized for a 3rd overtone oscillation by round blank. They also feature a built-in output buffer with high output drive capability and are available in miniature 6-pin package, making them ideal as DIP-type crystal oscillators.

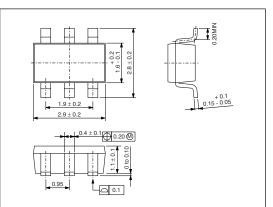
# **FEATURES**

- Operating supply voltage range
  - 3V operation: 2.7 to 3.6V
  - 5V operation: 4.5 to 5.5V
- 4MHz to 70MHz operating frequency range (Oscillation frequency is settable by external components)
- -40 to 85°C operating temperature range
- Oscillator capacitors C<sub>G</sub>, C<sub>D</sub> built-in (BN×H version only)
- Cutoff frequency setting using external feedback resistor  $R_{fo}$
- Output drive capability
  - $8mA(V_{DD} = 2.7V)$
  - $16mA(V_{DD} = 4.5V)$
- Output three-state function built-in
- High impedance output in standby mode
- CMOS output duty level (1/2VDD)
- Molybdenum-gate CMOS process
- Package: SOT23-6 (SM5023×××H)

## SERIES CONFIGURATION

# PACKAGE DIMENSIONS

(Unit: mm)



# **APPLICATIONS**

DIP-type crystal oscillator modules

	Operating	Recommended	Oscillator circuit constants				_	Standby mode	
Version	Supply voltage	voltage frequency			uilt-in capacitance		Output duty level	0	Output
	range [V]		gm ratio	C <sub>G</sub> [pF]	C <sub>D</sub> [pF]	Rf [kΩ]	uuty lovol	Oscillator	state
SM5023BNDH	2.7 to 3.6	- 22 to 70	3	8	15	-	CMOS	Operation	Hi-Z
SIVISUZSBINDH	4.5 to 5.5								LI-7
SM5023BNEH	2.7 to 3.6	50 to 70	4	8	12	-	CMOS	Operation	Hi-Z
	2.7 to 3.6	4 += 70	3	-			CMOS	Operation	Hi-Z
SM5023CNDH	4.5 to 5.5	4 to 70	3		_	-	CINICS	Operation	п- <i>2</i>

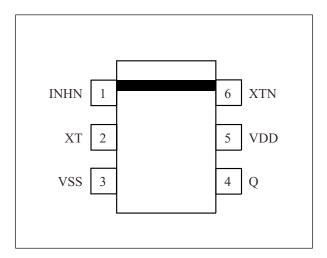
 The 3rd overtone frequency range using an external resistor to set the cutoff frequency. The recommended operating frequency is a yardstick value derived from the crystal used for NPC characteristics authentication. However, the oscillator frequency band is not guaranteed. Specifically, the characteristics can vary greatly due to crystal characteristics and mounting conditions, so the oscillation characteristics of components must be carefully evaluated.

# **ORDERING INFORMATION**

Device	Package			
SM5023×××H	SOT23-6			

# PINOUT

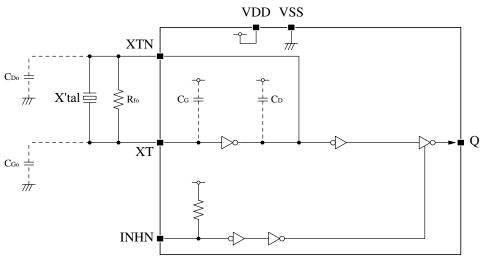
(Top view)



# **PIN DESCRIPTION**

Name	I/O	Description					
INHN	I	Output state control input. I Pull-up resistor built-in.	Dutput state control input. High impedance when LOW. Pull-up resistor built-in.				
ХТ	I	Amplifier input	Crystal connection pins.				
XTN	0	Amplifier output	Crystal is connected between XT and XTN.				
VSS	-	Ground	•				
Q	0	Output. f <sub>O</sub> (XT pin input free	quency)				
VDD	-	Supply voltage					

# **BLOCK DIAGRAM**



INHN = LOW active

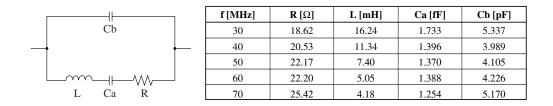
# **FUNCTIONAL DESCRIPTION**

## **Standby Function**

When INHN goes LOW, the oscillator output on Q becomes high impedance.

INHN	Q	Oscillator		
HIGH (or open)	f <sub>O</sub>	Normal operation		
LOW	High impedance	Normal operation		

## Current consumption and Output waveform with NPC's standard crystal



# SPECIFICATIONS

#### **Absolute Maximum Ratings**

 $V_{SS} = 0V$ 

Parameter	Symbol	Rating	Unit
Supply voltage range	V <sub>DD</sub>	-0.5 to +7.0	V
Input voltage range	V <sub>IN</sub>	–0.5 to V <sub>DD</sub> + 0.5	V
Output voltage range	V <sub>OUT</sub>	–0.5 to V <sub>DD</sub> + 0.5	V
Operating temperature range	T <sub>opr</sub>	-40 to +85	°C
Storage temperature range	T <sub>STG</sub>	-55 to +125	°C
Output current	I <sub>OUT</sub>	20	mA
Power dissipation	PD	250	mW

# **Recommended Operating Conditions**

### 3V operation: SM5023BNDH, BNEH, CNDH

 $V_{SS} = 0V$ ,  $f \le 70MHz$ ,  $C_L \le 15pF$  unless otherwise noted.

Parameter	Symbol		Unit		
Operating supply voltage	V <sub>DD</sub>	2.7	-	3.6	V
Input voltage	V <sub>IN</sub>	V <sub>SS</sub>	-	V <sub>DD</sub>	V
Operating temperature	T <sub>OPR</sub>	-20	-	+80	°C

#### 5V operation: SM5023BNDH, CNDH

$$\label{eq:VSS} \begin{split} V_{SS} = 0 \text{V}, \, f \leq 50 \text{MHz}, \, C_L \leq 50 \text{pF} \text{ unless otherwise noted}. \\ V_{SS} = 0 \text{V}, \, f \leq 70 \text{MHz}, \, C_L \leq 15 \text{pF} \text{ unless otherwise noted}. \end{split}$$

Parameter	Symbol		Unit		
Operating supply voltage	V <sub>DD</sub>	4.5	-	5.5	V
Input voltage	V <sub>IN</sub>	V <sub>SS</sub>	-	V <sub>DD</sub>	V
Operating temperature	T <sub>OPR</sub>	-40	-	+85	°C

## **Electrical Characteristics**

## 3V operation: SM5023BNDH, BNEH, CNDH

 $V_{DD}$  = 2.7 to 3.6V,  $V_{SS}$  = 0V, Ta = -20 to +80°C unless otherwise noted.

Parameter	Sumbol	Condition		Unit			
Parameter	Symbol	Si Conation			typ	max	Unit
HIGH-level output voltage	V <sub>OH</sub>	Q: Measurement cct 1, V <sub>DD</sub> = 2.7V, I <sub>OH</sub> =	8mA	2.1	2.4	-	V
LOW-level output voltage	V <sub>OL</sub>	Q: Measurement cct 2, $V_{DD}$ = 2.7V, $I_{OL}$ =	8mA	-	0.3	0.5	V
HIGH-level input voltage	V <sub>IH</sub>	INHN			-	-	V
LOW-level input voltage	V <sub>IL</sub>	INHN		-	-	0.5	V
	Ιz	Q: Measurement cct 2, INHN = LOW, V <sub>DD</sub> = 3.3V	$V_{OH} = V_{DD}$	-	-	10	μA
Output leakage current			V <sub>OL</sub> = V <sub>SS</sub>	-	-	10	μA
Current consumption	I <sub>DD</sub>	Measurement cct 3, load cct 1, INHN = open, C <sub>L</sub> = 15pF, f = 70MHz		-	15	30	mA
INHN pull-up resistance	R <sub>UP</sub>	Measurement cct 4		25	100	250	kΩ
Built-in capacitance	C <sub>G</sub>	Design value. A monitor pattern on a wafer is tested.	SM5023BNDH SM5023BNEH	7.44	8	8.56	pF
		Design value.	SM5023BNDH	13.95	15	16.05	pF
		A monitor pattern on a wafer is tested.	SM5023BNEH	11.16	12	12.84	pF

#### 5V operation: SM5023BNDH, CNDH

 $V_{DD}$  = 4.5 to 5.5V,  $V_{SS}$  = 0V, Ta = -40 to +85°C unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
Parameter	Symbol			min	typ	max	Unit
HIGH-level output voltage	V <sub>OH</sub>	Q: Measurement cct 1, $V_{DD}$ = 4.5V, $I_{OH}$ =	16mA	3.9	4.2	-	V
LOW-level output voltage	V <sub>OL</sub>	Q: Measurement cct 2, $V_{DD}$ = 4.5V, $I_{OL}$ =	16mA	-	0.3	0.5	V
HIGH-level input voltage	V <sub>IH</sub>	INHN		2.0	-	-	V
LOW-level input voltage	V <sub>IL</sub>	INHN	-	-	0.8	V	
	Ιz	Q: Measurement cct 2, INHN = LOW, $V_{DD} = 5.5V$	$V_{OH} = V_{DD}$	-	-	10	μA
Output leakage current			V <sub>OL</sub> = V <sub>SS</sub>	-	-	10	μA
Querrat annum the	I <sub>DD1</sub>	Measurement cct 3, load cct 1, INHN = open	C <sub>L</sub> = 15pF f = 70MHz	-	20	40	mA
Current consumption	I <sub>DD2</sub>		C <sub>L</sub> = 50pF f = 50MHz	-	25	50	mA
INHN pull-up resistance	R <sub>UP</sub>	Measurement cct 4		25	100	250	kΩ
Built-in capacitance	C <sub>G</sub>	Design value. A monitor pattern on a wafer is tested.	SM5023BNDH	7.44	8	8.56	pF
	CD	Design value. A monitor pattern on a wafer is tested.	SM5023BNDH	13.95	15	16.05	pF

#### **Switching Characteristics**

#### 3V operation: SM5023BNDH, BNEH, CNDH

 $V_{DD} = 2.7$  to 3.6V,  $V_{SS} = 0V$ , Ta = -20 to +80°C unless otherwise noted.

Parameter	Symbol	Condition		Unit		
Parameter	Symbol	Condition	min	typ	max	Unit
Output rise time	t <sub>r1</sub>	Measurement cct 5, load cct 1, 0.1V_{DD} to 0.9V_{DD} , C_L = 15pF	-	2.5	5	ns
Output fall time	t <sub>f1</sub>	Measurement cct 5, load cct 1, 0.9V_{DD} to 0.1V_{DD} , C_L = 15pF	-	2.5	5	ns
Output duty cycle <sup>1</sup>	Duty1	Measurement cct 5, load cct 1, V_DD = 3.0V, Ta = 25°C, CL = 15pF, f $\leq$ 70MHz	45	-	55	%
Output disable delay time	t <sub>PLZ</sub>	Measurement cct 5, load cct 1, V <sub>DD</sub> = 3.0V, Ta = 25°C,	-	-	100	ns
Output enable delay time	t <sub>PZL</sub>	C <sub>L</sub> = 15pF	-	-	100	ns

1. The duty cycle characteristic is checked the sample chips of each production lot.

#### 5V operation: SM5023BNDH, CNDH

 $V_{DD}$  = 4.5 to 5.5V,  $V_{SS}$  = 0V, Ta = -40 to +85°C unless otherwise noted.

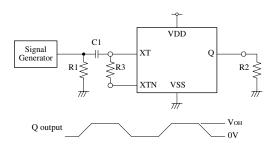
Parameter	Symbol	Condition	Rating			Unit	
Falanetei	Symbol				typ	max	Unit
Output rise time	t <sub>r1</sub>	Measurement cct 5, load cct 1,	C <sub>L</sub> = 15pF	-	1.5	3	20
	t <sub>r2</sub>	0.1V <sub>DD</sub> to 0.9V <sub>DD</sub>	C <sub>L</sub> = 50pF	-	3	6	ns
Output fall time	t <sub>f1</sub>	Measurement cct 5, load cct 1,	C <sub>L</sub> = 15pF	-	1.5	3	ns
	t <sub>f2</sub>	0.9V <sub>DD</sub> to 0.1V <sub>DD</sub>	C <sub>L</sub> = 50pF	-	3	6	115
Output duty cycle <sup>1</sup>	Duty1	Measurement cct 5, load cct 1,	$C_L = 15pF$ f $\leq$ 70MHz	45	-	55	%
	Duty2	$V_{DD} = 5.0V$ , Ta = 25°C	$C_L = 50 pF$ f $\leq 50 MHz$	45	-	55	%
Output disable delay time	t <sub>PLZ</sub>	Measurement cct 5, load cct 1, $V_{DD}$ = 5.0V, Ta = 25°C,		-	-	100	ns
Output enable delay time	Dutput enable delay time t <sub>PZL</sub> C <sub>L</sub> = 15pF		-	-	100	ns	

1. The duty cycle characteristic is checked the sample chips of each production lot.

## **MEASUREMENT CIRCUITS**

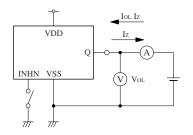
#### Measurement cct 1

#### Measurement cct 4

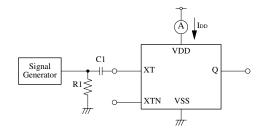


2.0Vp-p, 10MHz sine wave input signal (3V operation) 3.5Vp-p, 10MHz sine wave input signal (5V operation) C1:  $0.001\mu$ F R1:  $50\Omega$ R2:  $263\Omega$  (3V operation) 244 $\Omega$  (5V operation) R3:  $100k\Omega$ 

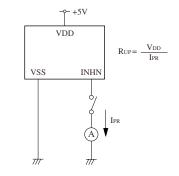
#### Measurement cct 2



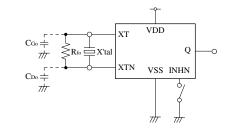
#### Measurement cct 3



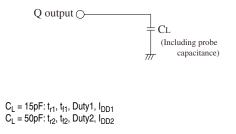
2.0Vp-p, 70MHz sine wave input signal (3V operation) 3.5Vp-p, 70MHz sine wave input signal (5V operation) C1: 0.001  $\mu F$  R1: 50  $\Omega$ 



#### Measurement cct 5

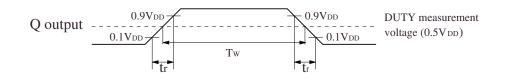


#### Load cct 1

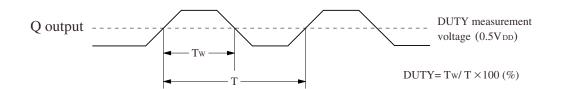


# Switching Time Measurement Waveform

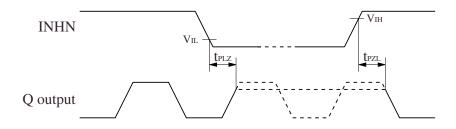
## Output duty level, t<sub>r</sub>, t<sub>f</sub>



Output duty cycle



# **Output Enable/Disable Delay**



INHN input waveform  $tr = tf \le 10ns$ 

SM5023 series

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